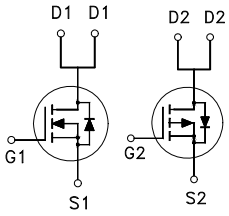
杰力科技股份有限公司
Excelliance MOS Corporation

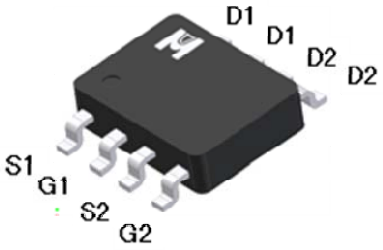
EMB17C03G

N & P-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

	N-CH	P-CH
BV_{DSS}	30V	-30V
$R_{DSON\ (MAX.)}$	17mΩ	20mΩ
I_D	10A	-8A





UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS		UNIT
Gate-Source Voltage		V_{GS}	N-CH	P-CH	V
			±20	±20	
Continuous Drain Current	T_C = 25 °C	I_D	10	-8	A
	T_C = 100 °C		7	-6	
Pulsed Drain Current[1]		I_{DM}	40	-32	
Avalanche Current		I_{AS}	10	-10	
Avalanche Energy	L = 0.1mH, ID=8A, RG=25Ω(N) L = 0.1mH, ID=-7A, RG=25Ω(P)	E_{AS}	3.2	2.45	mJ
Repetitive Avalanche Energy[2]	L = 0.05mH	E_{AR}	1.6	1.23	
Power Dissipation	T_C = 25 °C	P_D	2		W
	T_C = 100 °C		0.8		
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150		°C

100% UIS testing in condition of V_D=15V, L=0.1mH, V_G=10V, I_L=8A, Rated V_{DS}=30V N-CH

100% UIS testing in condition of V_D=15V, L=0.1mH, V_G=-10V, I_L=-7A, Rated V_{DS}=-30V P-CH

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		25	°C / W
Junction-to-Ambient[3]	$R_{\theta JA}$		62.5	

[1]Pulse width limited by maximum junction temperature.

[2]Duty cycle ≤ 1%

[3]62.5°C / W when mounted on a 1 in^2 pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS (T_C = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS		LIMITS			UNIT
				MIN	TYP	MAX	
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	N-CH	30			V
		V_{GS} = 0V, I_D = -250μA	P-CH	-30			
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	N-CH	1	1.5	3	
		V_{DS} = V_{GS}, I_D = -250μA	P-CH	-1	-1.5	-3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	N-CH			±100	nA
		V_{DS} = 0V, V_{GS} = ±20V	P-CH			±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V	N-CH			1	μA
		V_{DS} = -24V, V_{GS} = 0V	P-CH			-1	
		V_{DS} = 20V, V_{GS} = 0V, T_J = 125 °C	N-CH			25	
		V_{DS} = -20V, V_{GS} = 0V, T_J = 125 °C	P-CH			-25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	N-CH	10			A
		V_{DS} = -5V, V_{GS} = -10V	P-CH	-8			
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 10A	N-CH		14.5	17	mΩ
		V_{GS} = -10V, I_D = -8A	P-CH		17.5	20	
		V_{GS} = 4.5V, I_D = 6A	N-CH		21	26	
		V_{GS} = -4.5V, I_D = -6A	P-CH		26	35	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 10A	N-CH		18		S
		V_{DS} = -5V, I_D = -8A	P-CH		24		
DYNAMIC							
Input Capacitance	C_{iss}	N-CH V_{GS} = 0V, V_{DS} = 15V, f = 1MHz P=CH V_{GS} = 0V, V_{DS} = -15V, f = 1MHz	N-CH		597		pF
			P-CH		1407		
Output Capacitance	C_{oss}		N-CH		111		
			P-CH		208		
Reverse Transfer Capacitance	C_{rss}		N-CH		96		
			P-CH		164		

Gate Resistance	R_g	V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz	N-CH		2.0		Ω
			P-CH		4.0		
Total Gate Charge[1,2]	$Q_g(V_{GS}=10V)$ $Q_g(V_{GS}=-10V)$	N-CH V_{DS} = 15V, V_{GS} = 10V, I_D = 10A P-CH V_{DS} = -15V, V_{GS} = -10V, I_D = -8A	N-CH		14		nC
			P-CH		20.3		
	$Q_g(V_{GS}=4.5V)$ $Q_g(V_{GS}=-4.5V)$		N-CH		7.8		
			P-CH		9.8		
Gate-Source Charge[1,2]	Q_{gs}		N-CH		1.8		
			P-CH		3.2		
Gate-Drain Charge[1,2]	Q_{gd}		N-CH		4.7		
			P-CH		4.9		
Turn-On Delay Time[1,2]	$t_{d(on)}$	N-CH V_{DS} = 15V, I_D = 1A, V_{GS} = 10V, R_{GS} = 6Ω P-CH V_{DS} = -15V, I_D = -1A, V_{GS} = -10V, R_{GS} = 6Ω	N-CH		11		nS
			P-CH		10		
Rise Time[1,2]	t_r		N-CH		16		
			P-CH		8		
Turn-Off Delay Time[1,2]	$t_{d(off)}$		N-CH		36		
			P-CH		25		
Fall Time[1,2]	t_f		N-CH		20		
			P-CH		10		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)							
Continuous Current	I_S		N-CH			2.3	A
			P-CH			-2.3	
Pulsed Current[3]	I_{SM}		N-CH			9.2	
			P-CH			-9.2	
Forward Voltage[1]	V_{SD}	I_F = I_S, V_{GS} = 0V	N-CH			1.2	V
			P-CH			-1.2	
Reverse Recovery Time	t_{rr}	I_F = I_S, dI_F/dt = 100A / μS	N-CH		50		nS
			P-CH		32		
Peak Reverse Recovery Current	$I_{RM(REC)}$		N-CH		30		A
			P-CH		-28		
Reverse Recovery Charge	Q_{rr}		N-CH		20		nC
			P-CH		26		

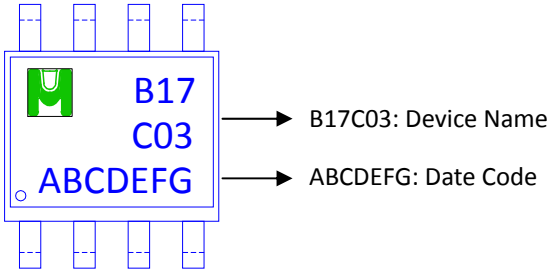
[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

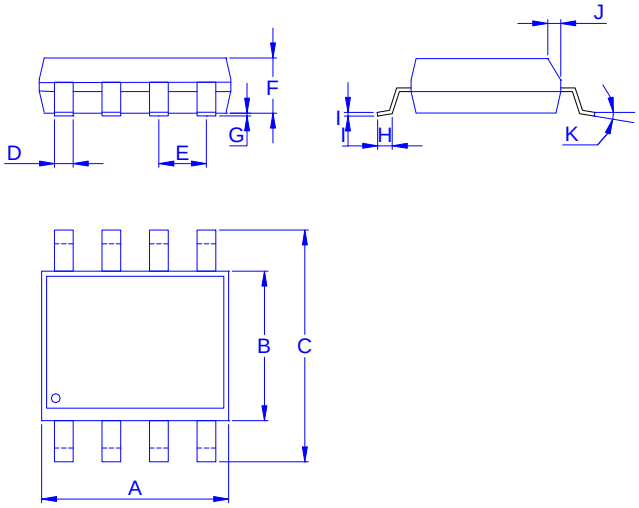
[3]Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMB17C03G for SOP-8



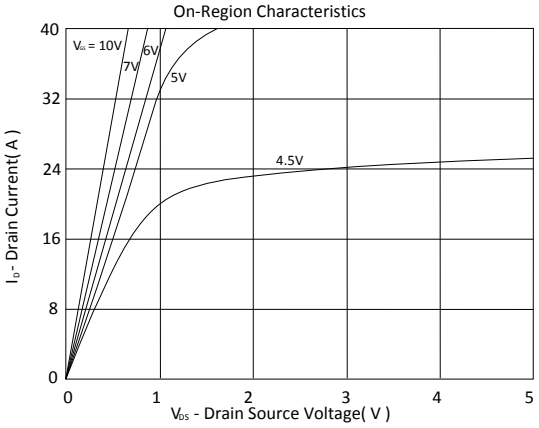
Outline Drawing

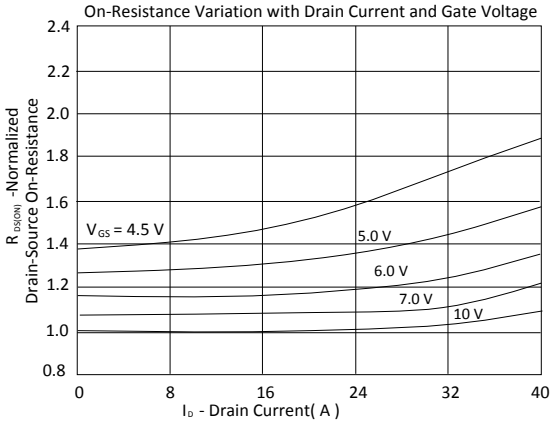


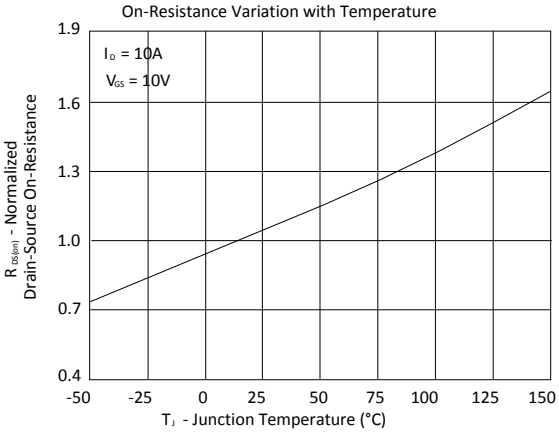
Dimension in mm

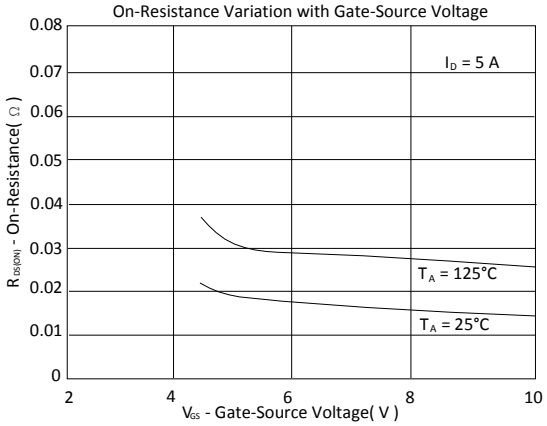
Dimension	A	B	C	D	E	F	G	H	I	J	K
Min.	4.70	3.70	5.80	0.33		1.20	0.08	0.40	0.19	0.25	0°
Typ.					1.27						
Max.	5.10	4.10	6.20	0.51		1.62	0.28	0.83	0.26	0.50	8°

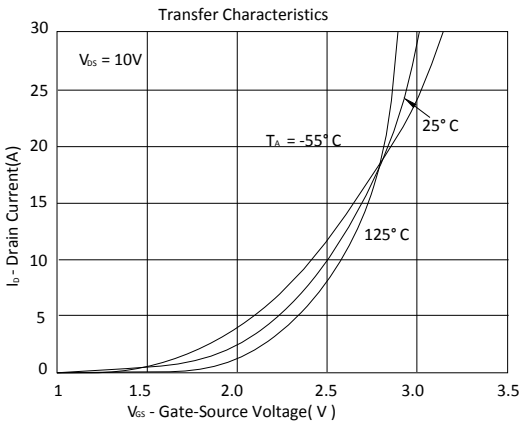
N-Channel

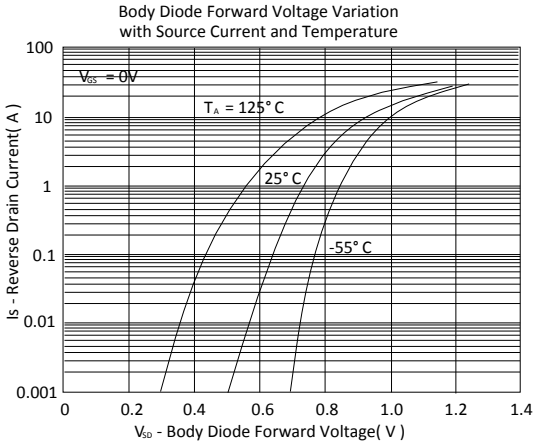

On-Region Characteristics
V_{GS} = 10V
7V
6V
5V
4.5V
I_D - Drain Current(A)
V_{DS} - Drain Source Voltage(V)


On-Resistance Variation with Drain Current and Gate Voltage
$R_{DS(ON)}$ -Normalized
Drain-Source On-Resistance
V_{GS} = 4.5 V
5.0 V
6.0 V
7.0 V
10 V
I_D - Drain Current(A)

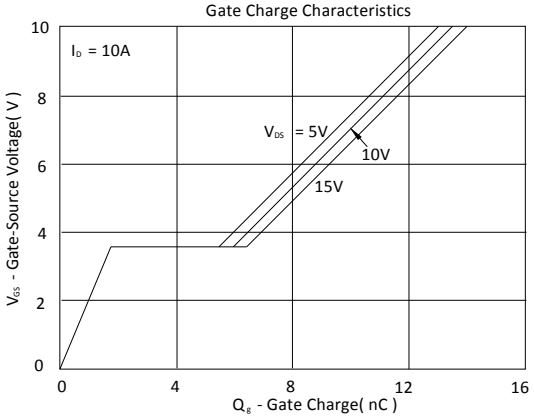

On-Resistance Variation with Temperature
I_D = 10A
V_{GS} = 10V
$R_{DS(on)}$ - Normalized
Drain-Source On-Resistance
T_J - Junction Temperature (°C)


On-Resistance Variation with Gate-Source Voltage
I_D = 5 A
$R_{DS(ON)}$ - On-Resistance(Ω)
T_A = 125°C
T_A = 25°C
V_{GS} - Gate-Source Voltage(V)

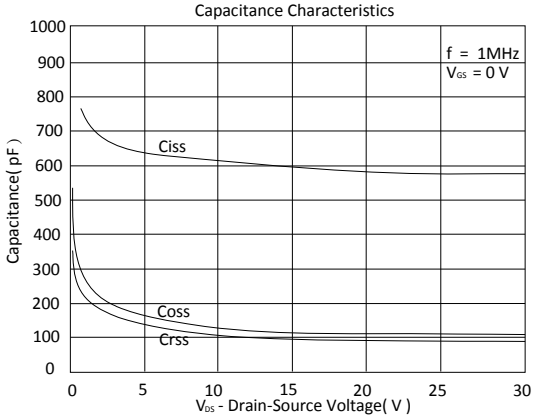

Transfer Characteristics
V_{DS} = 10V
T_A = -55° C
25° C
125° C
I_D - Drain Current(A)
V_{GS} - Gate-Source Voltage(V)


Body Diode Forward Voltage Variation
with Source Current and Temperature
V_{GS} = 0V
T_A = 125° C
25° C
-55° C
Is - Reverse Drain Current(A)
V_{SD} - Body Diode Forward Voltage(V)

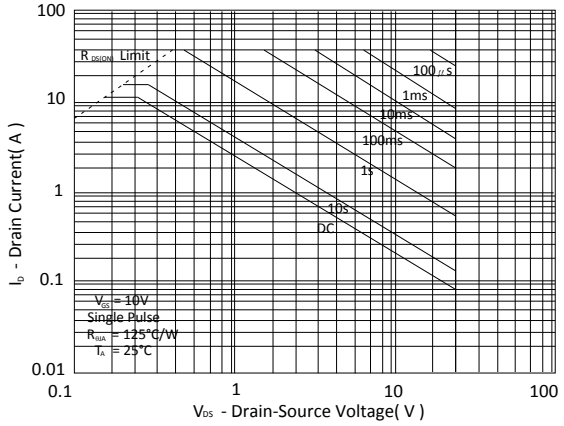
Gate Charge Characteristics



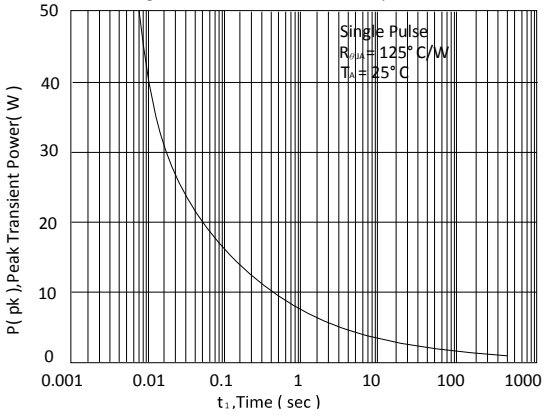
Capacitance Characteristics



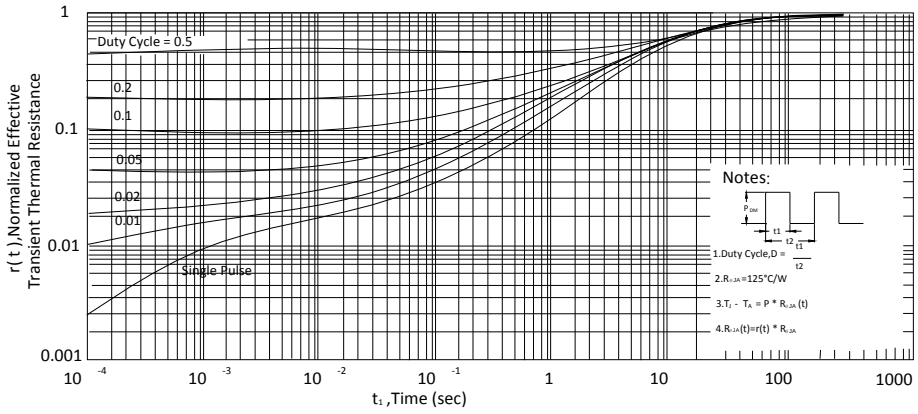
Maximum Safe Operating Area



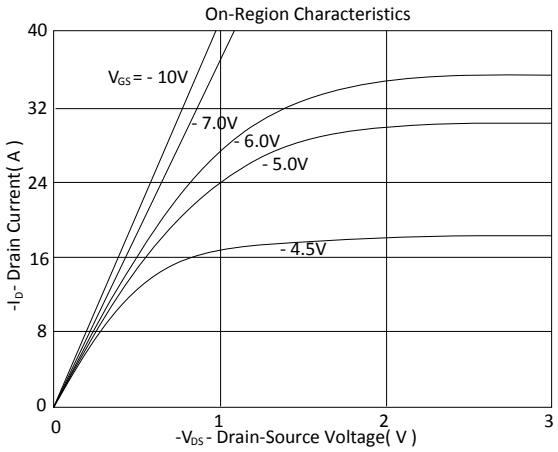
Single Pulse Maximum Power Dissipation

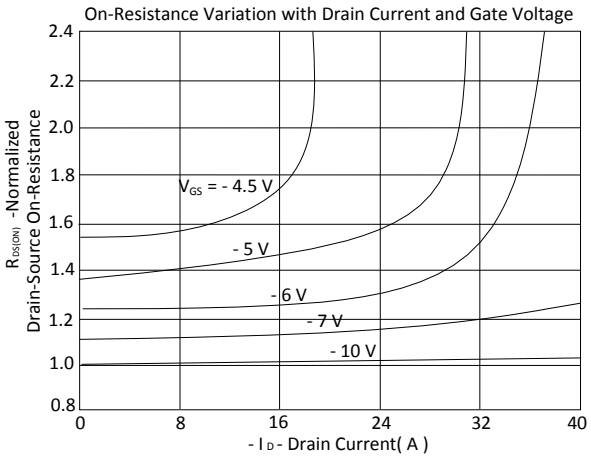


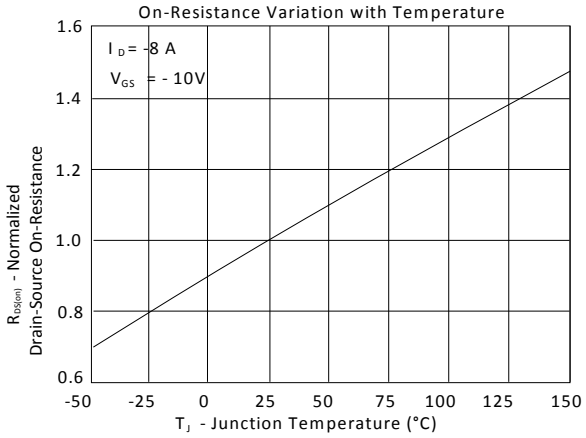
Transient Thermal Response Curve

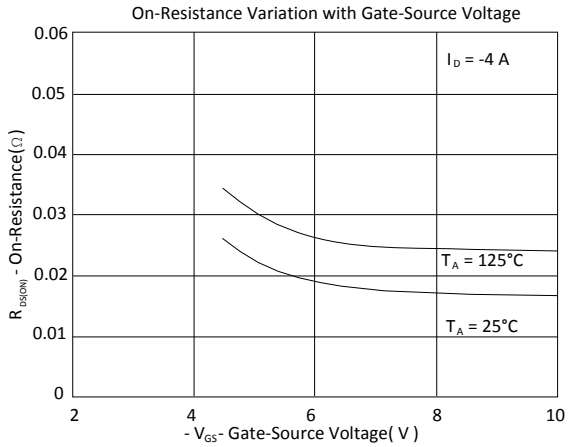


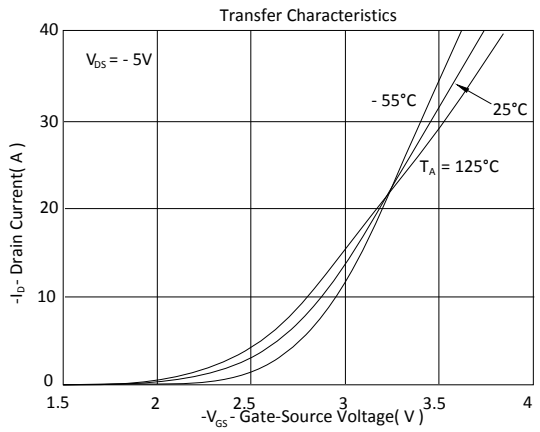
P-Channel

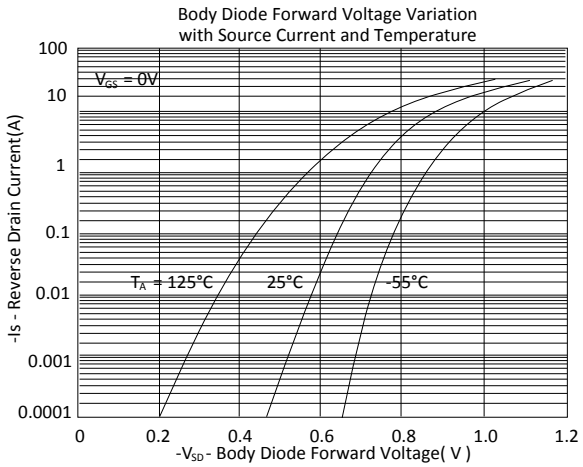

On-Region Characteristics
V_{GS} = - 10V
- 7.0V
- 6.0V
- 5.0V
- 4.5V
$-I_D$ - Drain Current(A)
$-V_{DS}$ - Drain-Source Voltage(V)


On-Resistance Variation with Drain Current and Gate Voltage
V_{GS} = - 4.5 V
- 5 V
- 6 V
- 7 V
- 10 V
$R_{DS(ON)}$ -Normalized
Drain-Source On-Resistance
$-I_D$ - Drain Current(A)

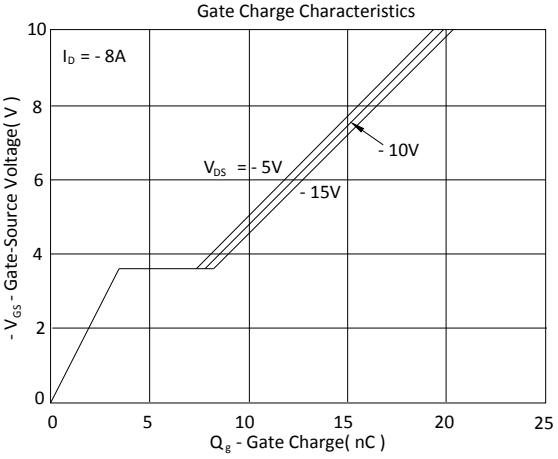

On-Resistance Variation with Temperature
I_D = -8 A
V_{GS} = - 10V
$R_{DS(on)}$ - Normalized
Drain-Source On-Resistance
T_J - Junction Temperature (°C)


On-Resistance Variation with Gate-Source Voltage
I_D = -4 A
T_A = 125°C
T_A = 25°C
$R_{DS(ON)}$ - On-Resistance(Ω)
$-V_{GS}$ - Gate-Source Voltage(V)

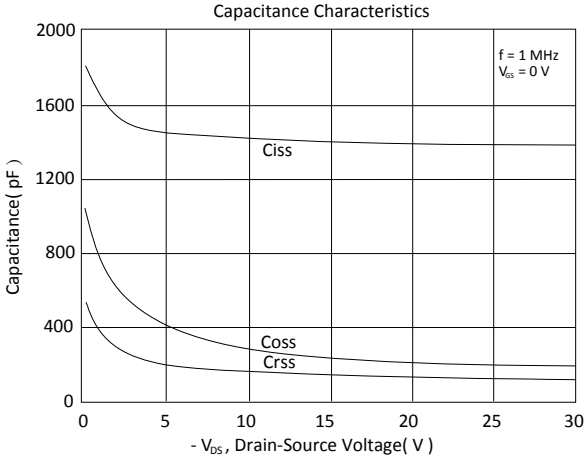

Transfer Characteristics
V_{DS} = - 5V
- 55°C
25°C
T_A = 125°C
$-I_D$ - Drain Current(A)
$-V_{GS}$ - Gate-Source Voltage(V)


Body Diode Forward Voltage Variation
with Source Current and Temperature
V_{GS} = 0V
T_A = 125°C
25°C
-55°C
-Is - Reverse Drain Current(A)
$-V_{SD}$ - Body Diode Forward Voltage(V)

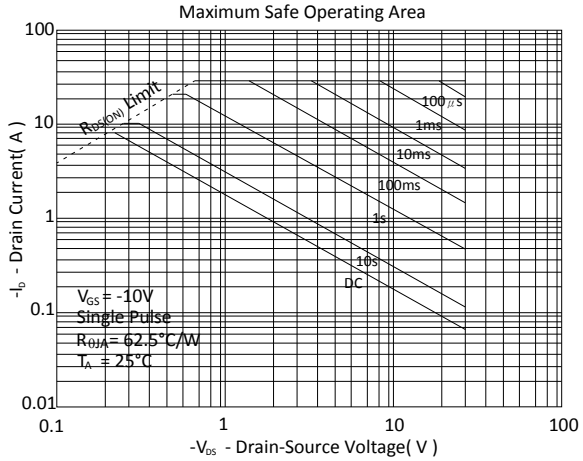
Gate Charge Characteristics



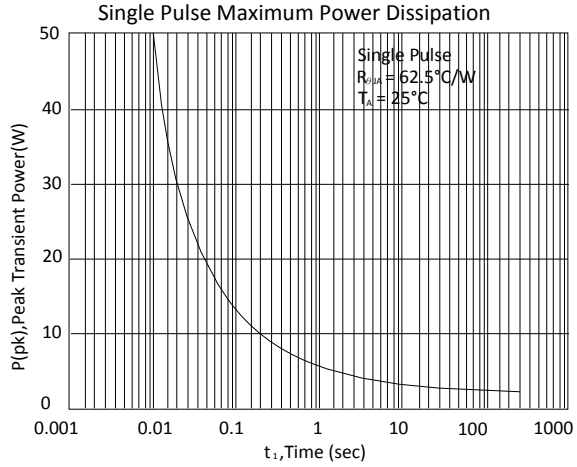
Capacitance Characteristics



Maximum Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve